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Electronics Science

Multi-Terminal NEM Switch Based On Compressible Molecules (Squitch)

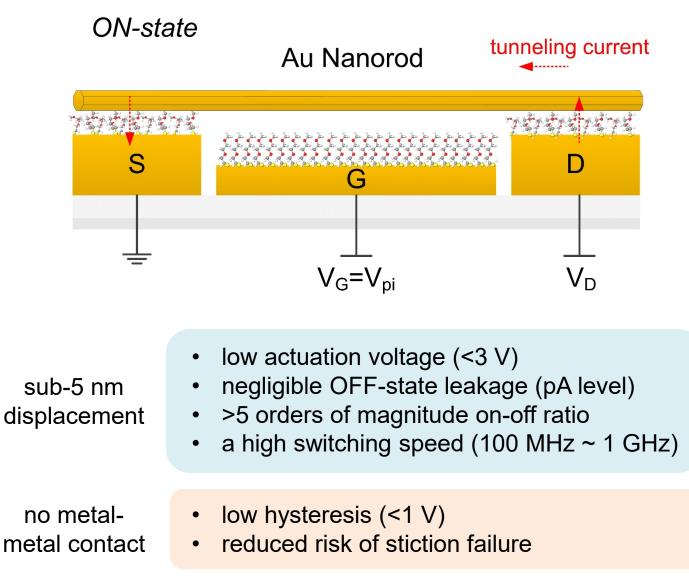
Jinchi Han (speaker) Dr. Farnaz Niroui

Advisors: Prof. Vladimir Bulović Prof. Jeffrey H. Lang

Collaborators: Prof. Timothy M. Swager

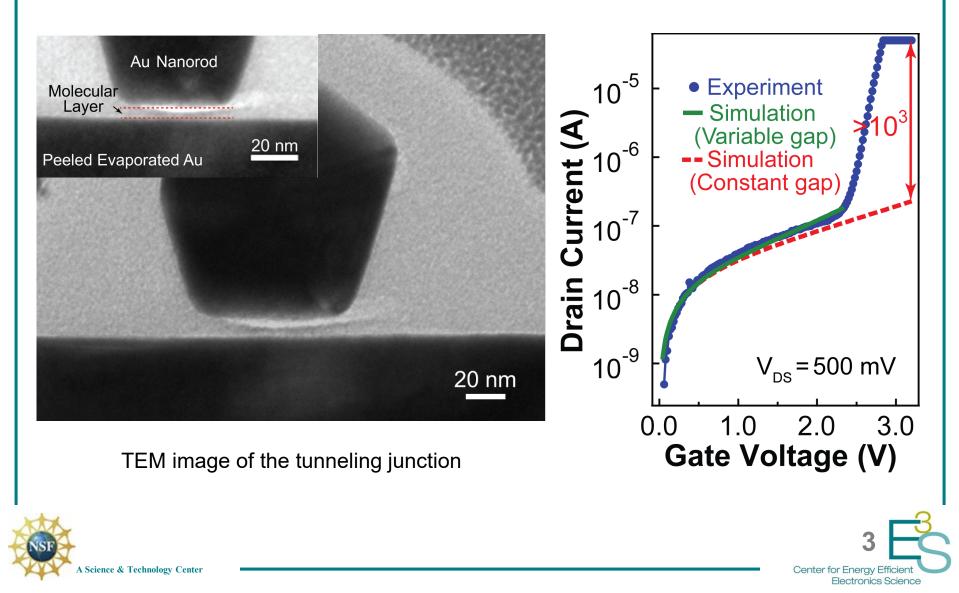
Prof. Jing Kong







Previous results on a multi-terminal squitch







Step 1 – patterning bottom electrodes **Yield** – 90%~100% **Design A** Design B 200 nm 200 nm



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Step 2 – pattern transfer by peeling

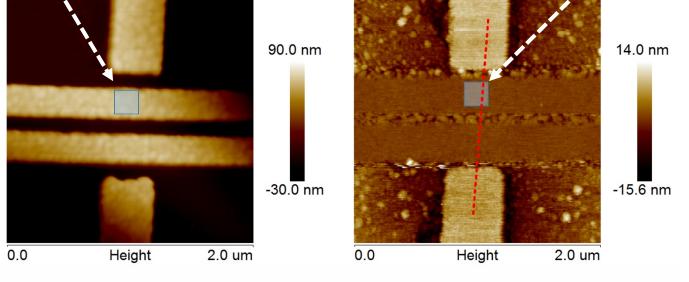
Yield - 90%~100%

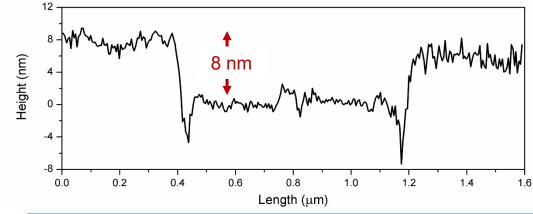
Roughness: 2.58 nm (RMS) Roughness: 0.44 nm (RMS)

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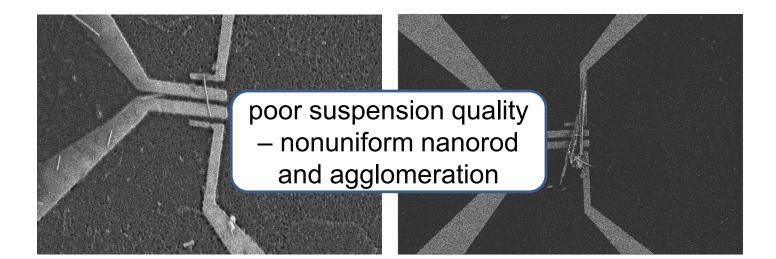
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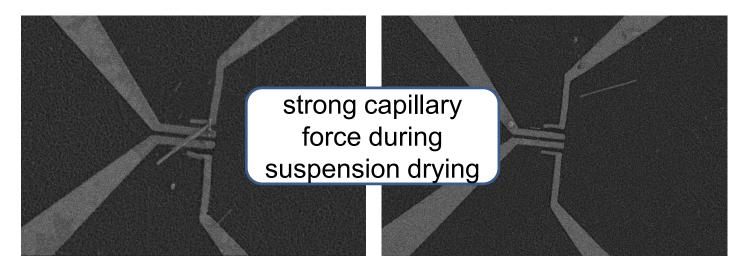






Step 4 – dielectrophoretic trapping top electrode

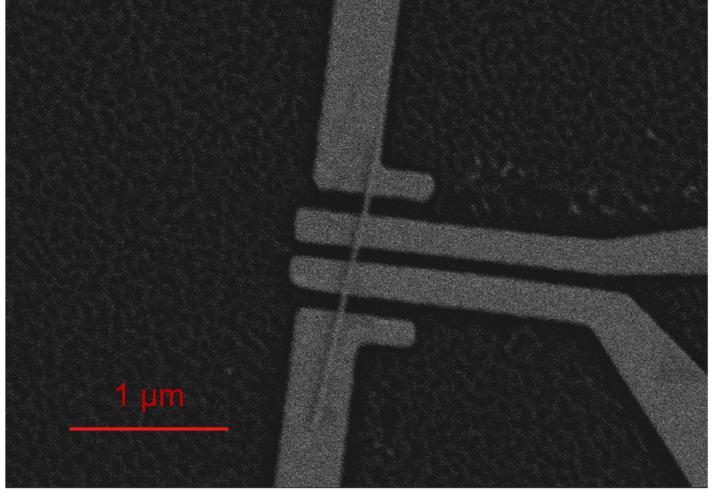






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Step 4 – dielectrophoretic trapping top electrode

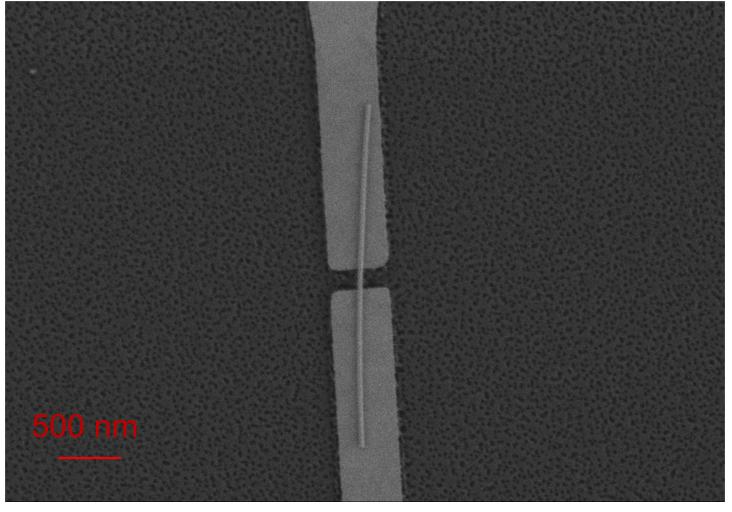






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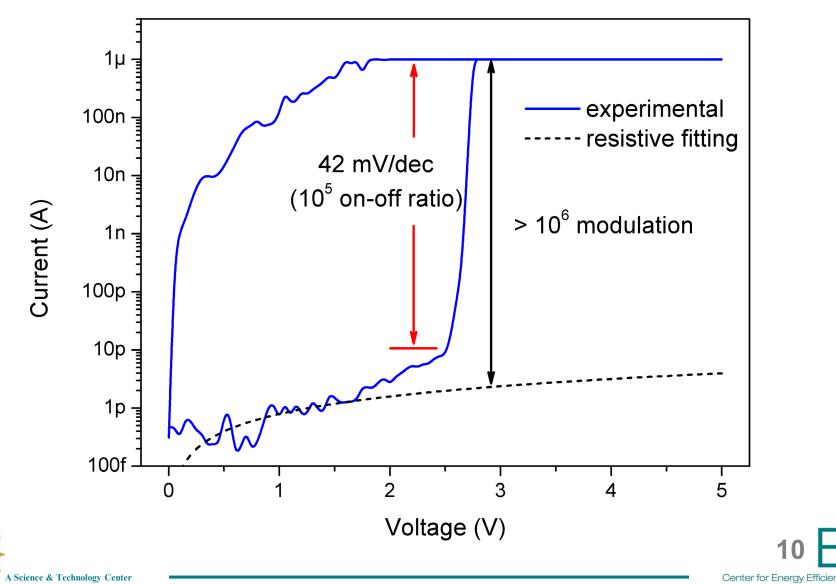
Experiments on two-terminal squitches







IV curve of two-terminal squitch



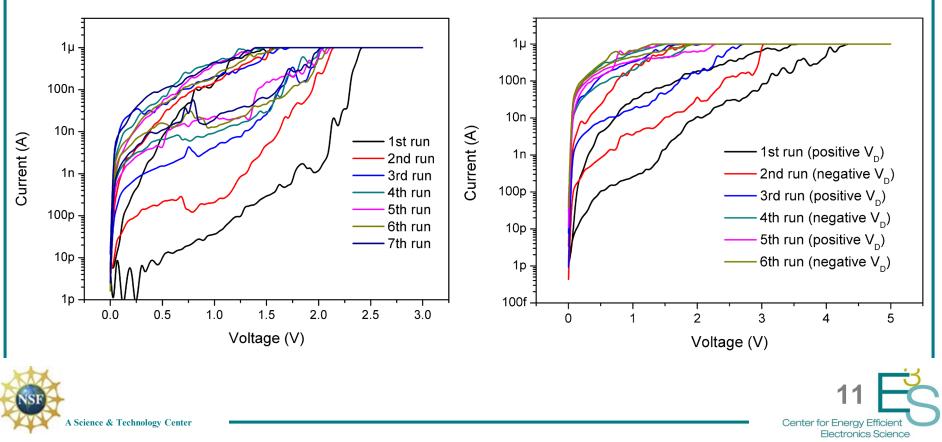
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Degradation in performance over cycles

 IV curves move towards upper left over cycles until stabilized or stiction due to change in

the elastic property, and the thickness of molecular layer

after cycles of compression



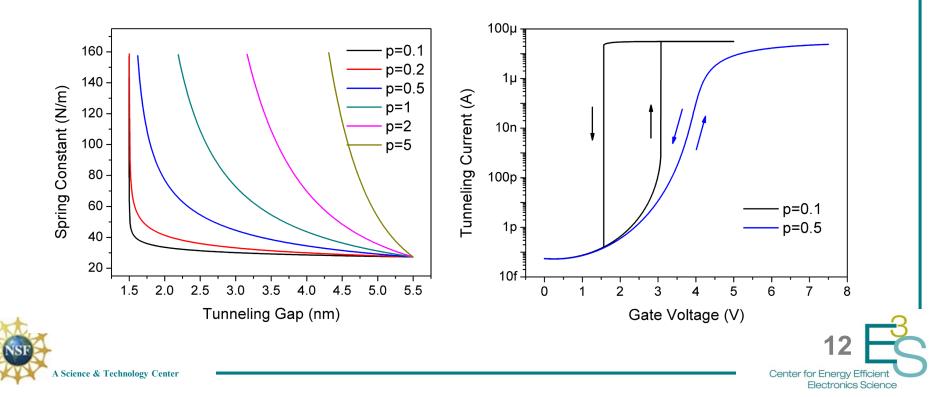
Squitch modeling

equivalent spring constant of molecular layer

$$k_{\rm f}(d_{\rm S,D}) = \left(\frac{d_0 - d_{\rm thr}}{d_{\rm S,D} - d_{\rm thr}}\right)^p \frac{E_{\rm m}S_{\rm S,D}}{d_0}$$

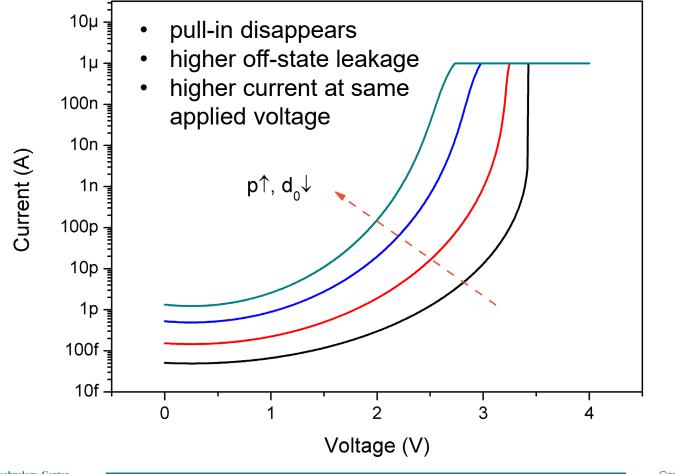
- d_{thr} : critical thickness when abrupt stiffening occurs
- E_m : Young's modulus of uncompressed molecules

 $S_{S,D}$: area of the source (S) or the drain (D)



Squitch modeling

Over cycles of compression, molecular layer becomes thinner (d_0 \downarrow) and molecules stiffen gradually (p^)





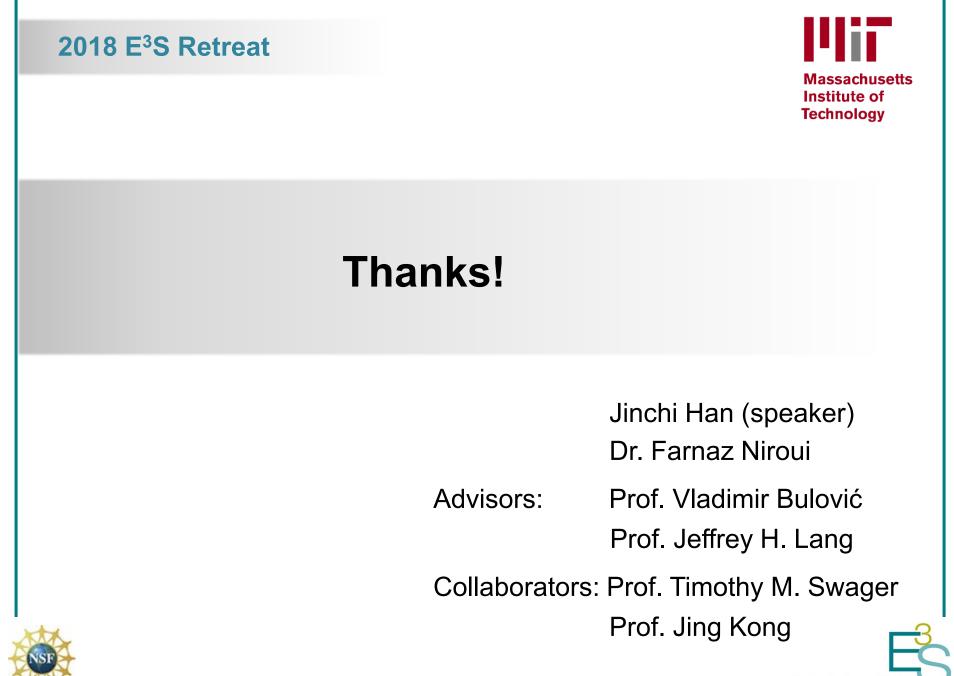
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Future work

- Further investigation on degradation of molecular layer factors include quality of assembly, accumulative joule heating, oxidization, effect of moisture, etc.
- 2. <u>Graphene-based multi-terminal squitch</u> replace Au nanorod with graphene and eliminate the trapping step towards a high throughput (permits more rapid experimentation on molecular behavior and circuit implementation)
- 3. <u>Study on dynamics of squitch</u> theoretical and experimental evaluation of switching delay







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